Silicon PNP Power Transistors 2SA1670

DESCRIPTION

·With TO-3PML package

·Complement to type 2SC4385

APPLICATIONS

·Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

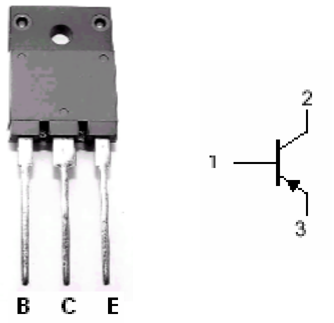

Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-6	A
I_B	Base current		-3	A
P_C	Collector power dissipation	T_C=25℃	60	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA; I_B=0	-80			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-2 A;I_B=-0.2 A			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-80V; I_E=0			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-10	μA
h_{FE}	DC current gain	I_C=-2A ; V_{CE}=-4V	50			
f_T	Transition frequency	I_C=-0.5A ; V_{CE}=-12V		20		MHz

Switching times

t_{on}	Turn-on time	I_C=-3A;R_L=10Ω I_{B1}=-I_{B2}=-0.3A V_{CC}=-30V		0.25		μs
t_{stg}	Storage time			0.5		μs
t_f	Fall time			0.1		μs

Silicon PNP Power Transistors 2SA1670

PACKAGE OUTLINE

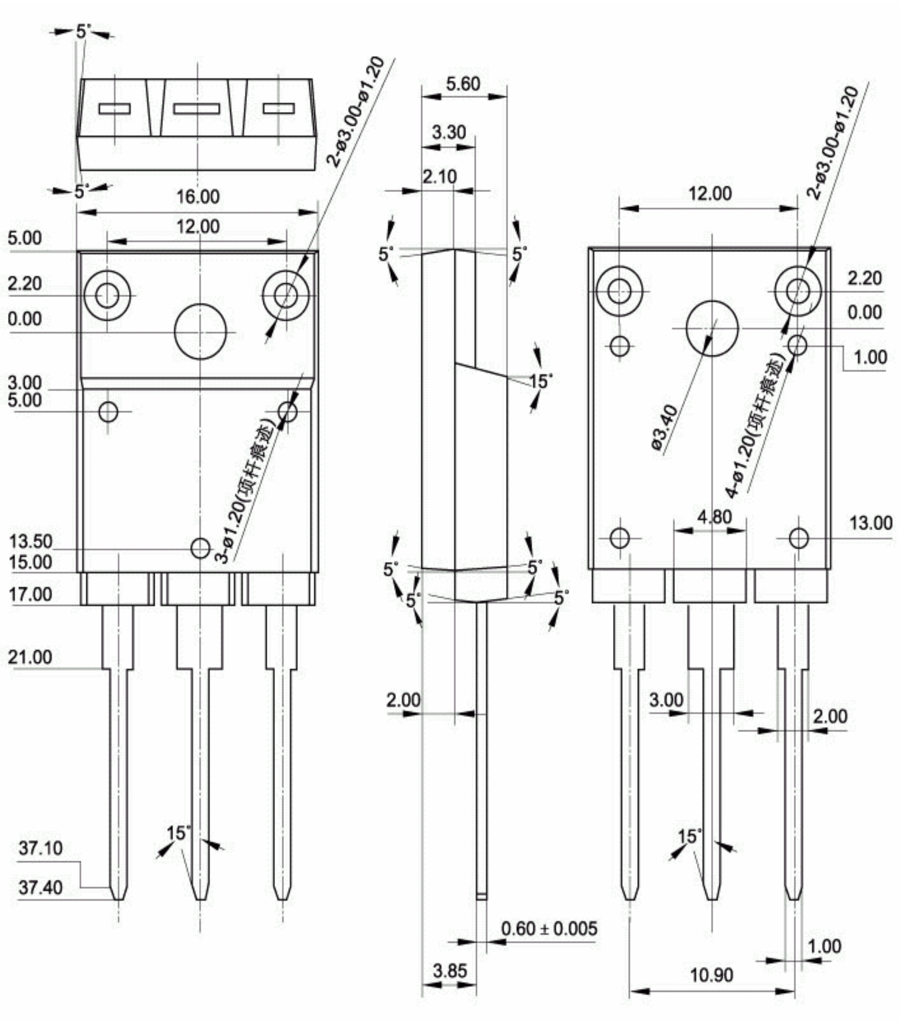

Fig.2 Outline dimensions